



## MICROPOWER PHASE-LOCKED LOOP

- QUIESCENT CURRENT SPECIFIED TO 20V FOR HCC DEVICE
- VERY LOW POWER CONSUMPTION : 100μW (TYP.) AT VCO f<sub>o</sub> = 10kHz, V<sub>DD</sub> = 5V
- OPERATING FREQUENCY RANGE : UP TO 1.4MHz (TYP.) AT V<sub>DD</sub> = 10V
- LOW FREQUENCY DRIFT : 0.06%/°C (typ.) AT V<sub>DD</sub> = 10V
- CHOICE OF TWO PHASE COMPARATORS :
  1) EXCLUSIVE OR NETWORK
  2) EDGE-CONTROLLED MEMORY NETWORK
  WITH PHASE-PULSE OUTPUT FOR LOCK INDICATION
- HIGH VCO LINEARITY : 1% (TYP.)
- VCO INHIBIT CONTROL FOR ON-OFF KE-YING AND ULTRA-LOW STANDBY POWER CONSUMPTION
- SOURCE-FOLLOWER OUTPUT OF VCO CONTROL INPUT (demod. output)
- ZENER DIODE TO ASSIST SUPPLY REGULA-TION
- 5V, 10V AND 15V PARAMETRIC RATING
- INPUT CURRENT OF 100nA AT 18V AND 25°C FOR HCC DEVICE
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDECTEN-TATIVE STANDARD N°. 13A, "STANDARD SPECIFICATIONS FOR DESCRIPTION OF "B" SERIES CMOS DEVICES"

#### DESCRIPTION

The **HCC4046B** (extended temperature range) and **HCF4046B** (intermediate temperature range) are monolithic integrated circuits, available in 16-lead dual in-line plastic or ceramic package. The **HCC/HCF4046B** COS/MOS Micropower Phase-Locked Loop (PLL) consists of a low-power, linear voltage-controlled oscillator (VCO) and two different phase comparators having a common signal-input amplifier and a common comparator input. A 5.2V zener diode is provided for supply regulation if necessary.









#### **VCO Section**

The VCO requires one external capacitor C1 and one or two external resistors (R1 or R1 and R2). Resistor R1 and capacitor C1 determine the frequency range of the VCO and resistor R2 enables the VCO to have a frequency offset if required. The high input impedance (10  $^{12\Omega}$  ) of the VCO simplifiers the design of low-pass filters by permitting the designer a wide choice of resistor-to-capacitor ratios. In order not to load the low-pass filter, a source-follower output of the VCO input voltage is provided at terminal 10 (DE-MODULATED OUTPUT). If this terminal is used, a load resistor (Rs) of 10 kΩ or more should be connected from this terminal to VSS. If unused this terminal should be left open. The VCO can be connected either directly or through frequency dividers to the comparator input of the phase comparators. A full COS/MOS logic swing is available at the output of the VCO and allows direct coupling to COS/MOS frequency dividers such as the HCC/HCF4024B, HCC/HCF4018B, HCC/HCF4020B,

HCC/HCF4022B, HCC/HCF4029B, and

**HBC/HBF4059A**. One or more **HCC/HCF4018B** (Presettable Divide-by-N Counter) or **HCC/HCF4029B** (Presettable Up/Down Counter), or **HBC/HBF4059A** (Programmable Divide-by-"N" Counter), together with the **HCC/HCF4046B** (Phase-Locked Loop) can be used to build a micropower low-frequency synthesizer. A logic 0 on the INHIBIT input "enables" the VCO and the source follower, while a logic 1 "turns off" both to minimize stand-by power consumption.

#### **Phase Comparators**

The phase-comparator signal input (terminal 14) can be direct-coupled provided the signal swing is within COS/MOS logic levels [logic "0"  $\leq$  30 %  $(V_{DD} - V_{SS})$ , logic "1"  $\geq$  70 %  $(V_{DD} - V_{SS})$ ]. For smaller swings the signal must be capacitively coupled to the self-biasing amplifier at the signal input. Phase comparator I is an exclusive-OR network ; it operates analagously to an over-driven balanced mixer. To maximize the lock range, the signal-and comparator-input frequencies must have a 50% duty cycle. With no signal or noise on the signal input, this phase comparator has an average output voltage equal to V<sub>DD</sub>/2. The low-pass filter connected to the output of phase comparator I supplies the averaged voltage to the VCO input, and causes the VCO to oscillate at the center frequency (f<sub>o</sub>). The frequency range of input signals on which the PLL will lock if it was initially out of lock is defined as the frequency capture range (2 fc). The frequency range of input signals on which the loop will stay locked if it was initially in lock is defined as the frequency lock range (2 f<sub>L</sub>). The capture range is  $\leq$  the

lock range. With phase comparator I the range of frequencies over which the PLL can acquire lock (capture range) is dependent on the low-pass-filter characteristics, and can be made as large as the lock range. Phase-comparator I enables a PLL system to remain in lock in spite of high amounts of noise in the input signal. One characteristic of this type of phase comparator is that it may lock onto input frequencies that are close to harmonics of the VCO center-frequency. A second characteristic is that the phase angle between the signal and the comparator input varies between 0° and 180°, and is 90° at the center frequency. Fig. (a) shows the typical, triangular, phase-to-output response characteristic of phase-comparator I. Typical waveforms for a COS/MOS phase-locked-loop employing phase comparator I in locked condition of fo is shown in fig. (b). Phase-comparator II is an edge-controlled digital memory network. It consists of four flip-flop stages, control gating, and a three-stage output-circuit comprising p- and n-type drivers having a common output node. When the p-MOS or n-MOS drivers are ON they pull the output up to VDD or down to V<sub>SS</sub>, respectively. This type of phase comparator acts only on the positive edges of the signal and comparator inputs. The duty cycles of the signal and comparator inputs are not important since positive transitions control the PLL system utilizing this type of comparator. If the signal-input frequency is higher than the comparator-input frequency, the p-type output driver is maintained ON most of the time, and both the n- and p-drivers OFF (3 state) the remainder of the time. If the signal-input frequency is lower than the comparator-input frequency, the n-type output driver is maintained ON most of the time, and both the n- and p-drivers OFF (3 state) the remainder of the time. If the signal and comparator-input frequencies are the same, but the signal input lags the comparator input in phase, the n-type output driver is maintained ON for a time corresponding to the phase difference. If the signal and comparatorinput frequencies are the same, but the comparator input lags the signal in phase, the p-type output driver is maintained ON for a time corresponding to the phase difference. Subsequently, the capacitor voltage of the low-pass filter connected to this phase comparator is adjusted until the signal and comparator inputs are equal in both phase and freguency. At this stable point both p- and n-type output drivers remain OFF and thus the phase comparator output becomes an open circuit and holds the voltage on the capacitor of the low-pass filter constant. Moreover the signal at the "phase pulses" output is a high level which can be used for indicating a locked condition. Thus, for phase comparator II, no phase difference exists between signal and comparator

input over the full VCO frequency range. Moreover, the power dissipation due to the low-pass filter is reduced when this type of phase comparator is used because both the p- and n-type output drivers are OFF for most of the signal input cycle. It should be noted that the PLL lock range for this type of phase

Figure a : Phase-Comparator I Characteristics at Low-Pass Filter Output.

comparator is equal to the capture range, independent of the low-pass filter. With no signal present at the signal input, the VCO is adjusted to its lowest frequency for phase comparator II. Fig. (c) shows typical waveforms for a COS/MOS PLL employing phase comparator II in a locked condition.

Figure b : Typical Waveforms for COS/MOS Phase Locked-Loop Employing Phase Comparator I in Locked Condition of fo.



Figure C : Typical Waveforms For COS/MOS Phase-locked Loop Employing Phase Comparator II In Locked Condition.



#### **FUNCTIONAL DIAGRAM**



#### **ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
V <sub>DD</sub> *	Supply Voltage : HCC Types HCF Types	- 0.5 to + 20 - 0.5 to + 18	V V
Vi	Input Voltage	- 0.5 to V <sub>DD</sub> + 0.5	V
l <sub>l</sub>	DC Input Current (any one input)	± 10	mA
P <sub>tot</sub>	Total Power Dissipation (per package) Dissipation per Output Transistor for $T_{op}$ = Full Package-temperature Range	200 100	mW mW
T <sub>op</sub>	Operating Temperature : HCC Types HCF Types	- 55 to + 125 - 40 to + 85	℃ ℃
T <sub>stg</sub>	Storage Temperature	- 65 to + 150	°C

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for external periods may affect device reliability. \* All voltage values are referred to V<sub>SS</sub> pin voltage.

#### **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Value	Unit
V <sub>DD</sub>	Supply Voltage : HCC Types HCF Types	3 to 18 3 to 15	> >
VI	Input Voltage	0 to V <sub>DD</sub>	V
T <sub>op</sub>	Operating Temperature : HCC Types HCF Types	– 55 to + 125 – 40 to + 85	ΰŐ

			т	est Con	<u>dition</u>	s				Value				
Symbol	Parame	ter	Vi	٧o	llol	$V_{DD}$	TL	ow*		25°C		T <sub>Hi</sub>	igh <sup>*</sup>	Unit
-			(V)	(V)	(μΑ)	(V)	Min.	Max.	Min.	Тур.	Max.	Min.	Max.	
VCO S	ECTION													
V <sub>OH</sub>	Output High	า	0/5		< 1	5	4.95		4.95	5		4.95		
	Voltage		0/10		< 1	10	9.95		9.95	10		9.95		
			0/15		< 1	15	14.95		14.95	15		14.95		V
V <sub>OL</sub>	Output Low	,	5/0		< 1	5		0.05			0.05		0.05	v
	Voltage		10/0		< 1	10		0.05			0.05		0.05	
	Output		15/0 0/ 5	2.5	< 1	15 5	- 2	0.05	1.6	- 3.2	0.05	- 1.15	0.05	
I <sub>ОН</sub>	Drive	нсс	0/5	4.6		5	- <u>2</u> - 0.64		- 0.51			- 1.15 - 0.36		
	Current	Types		9.5		10	- 0.04 - 1.6		- 1.3			- 0.30 - 0.9		
		Types	0/10	13.5		15	- 4.2		- 3.4			- 2.4		
			0/13	2.5		5	- 1.53			- 3.2		- 1.1		
			0/5	4.6		5	- 0.52		- 0.44			- 0.36		
		Types		9.5		10	- 1.3		- 1.1	- 2.6		- 0.9		
		Typee	0/15	13.5		15	- 3.6		- 3.0	- 6.8		- 2.4		mA
I <sub>OL</sub>	Output		0/ 5	0.4		5	0.64		0.51	1		0.36		
IOL	Sink	нсс	0/10	0.5		10	1.6		1.3	2.6		0.9		
	Current	Types	0/15	1.5		15	4.2		3.4	6.8		2.4		
			0/5	0.4		5	0.52		0.44	1		0.36		
		HCF	0/10	0.5		10	1.3		1.1	2.6		0.9		
		Types	0/15	1.5		15	3.6		3.0	6.8		2.4		
I <sub>IH</sub> , I <sub>IL</sub>	Input	нсс	0/18			18		± 0.1		± 10 <sup>-5</sup>	± 0.1		± 1	
	Leakage Current	Types HCF		Any Inp		put		-						μΑ
	Current	Types	0/15			15		± 0.3		$\pm 10^{-5}$	± 0.3		± 1	
PHASE	COMPARA			ON										
I <sub>DD</sub>	Total Device		0/5			5		0.1	1	0.05	0.1		0.1	
עטי	Current	, ,	0/10			10		0.5		0.25	0.5		0.5	
	Pin 14 = Ope	en	0/15			15		1.5		0.75	1.5		1.5	mA
	Pin 5 = $V_{DD}$		0/20			20		4		2	4		4	
	Pin 14 = $V_{SS}$		0/5			5		5		0.04	5		150	
	or V <sub>DD</sub>	HCC	0/10			10		10		0.04	10		300	
	Pin 5 = $V_{DD}$	Types				15		20		0.04	20		600	
			0/20			20		100		0.08	100		3000	μA
		HCF	0/5			5		20		0.04	20		150	
		Types	0/10			10		40		0.04	40		300	
		.,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	0/15			15		80		0.04	80		600	
I <sub>ОН</sub>	Output		0/5	2.5		5	- 2		- 1.6			- 1.15		
	Drive	HCC	0/5	4.6		5	- 0.64		- 0.51			- 0.36		
	Current	Types		9.5		10	- 1.6		- 1.3			- 0.9		
			0/15	13.5		15	- 4.2		- 3.4			- 2.4		mA
		ЦСЕ	0/5	2.5		5	- 1.53			- 3.2		- 1.1		
		HCF	0/5	4.6		5	- 0.52		- 0.44			- 0.36		
		0,10	9.5		10	- 1.3		- 1.1	- 2.6		- 0.9			
			0/15	13.5		15	- 3.6		- 3.0	- 6.8		- 2.4		

#### STATIC ELECTRICAL CHARACTERISTICS (over recommended operating conditions)

\*  $T_{Low} = -55^{\circ}C$  for HCC device :  $-40^{\circ}C$  for HCF device. \*  $T_{High} = +125^{\circ}C$  for HCC device :  $+85^{\circ}C$  for HCF device. The Noise Margin for both "1" and "0" level is : 1V min. with  $V_{DD} = 5V$ , 2V min. with  $V_{DD} = 10V$ , 2.5V min. with  $V_{DD} = 15V$ .

			Т	est Con	dition	S				Value				
Symbol	Parame	ter	VI	٧o	I <sub>0</sub>	$V_{DD}$	ΤL	ow*		25°C		Тн	igh <sup>*</sup>	Unit
_			(V)	(V)	(µA)	(V)	Min.	Max.	Min.	Тур.	Max.	Min.	Max.	
I <sub>OL</sub>	Output	нсс	0/ 5	0.4		5	0.64		0.51	1		0.36		
	Sink	Types	0/10	0.5		10	1.6		1.3	2.6		0.9		
	Current	Турсз	0/15	1.5		15	4.2		3.4	6.8		2.4		mA
		HCF	0/5	0.4		5	0.52		0.44	1		0.36		IIIA
		Types	0/10	0.5		10	1.3		1.1	2.6		0.9		
		турсз	0/15	1.5		15	3.6		3.0	6.8		2.4		
V <sub>IH</sub>	Input High			0.5/4.5	< 1	5	3.5		3.5			3.5		
	Voltage			1/9	< 1	10	7		7			7		V
				1.5/13.5	< 1	15	11		11			11		
VIL	Input Low			4.5/0.5	< 1	5		1.5			1.5		1.5	
	Voltage			9/1	< 1	10		3			3		3	V
				13.5/1.5	< 1	15		4			4		4	
I <sub>IH</sub> , I <sub>IL</sub>	Input Leakage Current	HCC Types	0/18	Any In	put	18		± 0.1		± 10 <sup>-5</sup>	± 0.1		± 1	μA
	(except. pin 14)	HCF Types	0/15	,,	par	15		± 0.3		± 10 <sup>-5</sup>	± 0.3		± 1	μι
I <sub>OUT</sub>	3-state Leakage	HCC Types	0/18	0/18		18		± 0.4		± 10 <sup>-4</sup>	± 0.4		± 12	μA
	Current	HCF Types	0/15	0/15		15		± 1.0		± 10 <sup>-4</sup>			± 7.5	7.5
CI	Input Capa	citance		Any In	put					5	7.5			рF

#### STATIC ELECTRICAL CHARACTERISTICS (continued)

\*  $T_{Low} = -55^{\circ}C$  for HCC device :  $-40^{\circ}C$  for HCF device. \*  $T_{High} = +125^{\circ}C$  for HCC device :  $+85^{\circ}C$  for HCF device. The Noise Margin for both "1" and "0" level is : 1V min. with  $V_{DD} = 5V$ , 2V min. with  $V_{DD} = 10V$ , 2.5V min. with  $V_{DD} = 15V$ .

ELECTRICAL CARACTERISTICS	$(T_{amb} = 25 \ ^{o}C)$	)
---------------------------	--------------------------	---

Symbol	Baramatar	Test Conditions			Value		Unit		
Symbol	Parameter		$V_{DD}$ (V)	Min.	Тур.	Max.	Unit		
VCO SE	CTION								
PD	Operating Power	fo = 10 KHz R1 = 10 M $\Omega$	5		70	140			
	Dissipation	$R2 = \infty \qquad V_{COIN} = \frac{V_{DD}}{2}$	10		800	1600	μW		
		2	15		3000	6000			
f <sub>max</sub>	Maximum Frequency	R1 = 10 KΩ C1 = 50 pF	5	0.3	0.6				
		$R2 = \infty$ $V_{COIN} = V_{DD}$	10	0.6	1.2				
			15	0.8	1.6		MH		
		R1 = 5 KΩ n C1 = 50 pF	5	0.5	0.8				
		$R2 = \infty$ $V_{COIN} = V_{DD}$	10	1	1.4				
			15	1.4	2.4				
	Center Frequency (f <sub>o</sub> ) and Frequency Range f <sub>max</sub> - f <sub>min</sub>	Programmable with external components R1, R2 and C1							
	Linearity	$V_{COIN}=2.5V^{\pm0.3}$ R1=10 K $\Omega$	5		1.7				
		V <sub>COIN</sub> =5V <sup>± 1</sup> R1=100 KΩ	10		0.5				
		V <sub>COIN</sub> =5V <sup>± 2.5</sup> R1=400 KΩ 10					%		
		$V_{\text{COIN}}\text{=}7.5\text{V}^{\pm1.5}~\text{R1}\text{=}100~\text{K}\Omega$	15		0.5				
		$V_{COIN}=7.5V^{\pm 5}$ R1=1 M $\Omega$	15		7				
	Temperature Frequency		5		±0.12				
	Stability (no frequency		10		±0.04				
	offset) f <sub>min</sub> = 0		15		±0.015		%/ <sup>0</sup>		
	Temperature Frequency		5		±0.09				
	Stability (frequency offset)		10		±0.07				
	f <sub>min</sub> ≠ 0		15		±0.03				
Vco	Output Duty Cycle		5, 10, 15		50		%		
t <sub>THL</sub>	VCO Output Transition		5		100	200			
t⊤∟н	Time		10		50	100	ns		
			15		40	80			
	Source Follower Output (demodulated Output): Offset Voltage V <sub>COIN</sub> - V <sub>DEM</sub>	R <sub>S</sub> > 10 KΩ	5, 10, 15		1.8	2.5	V		
	Source Follower Output	R <sub>S</sub> =100 KΩ V <sub>COIN</sub> =2.5 <sup>±0.3</sup> V	5		0.3				
	(demodulated Output):	R <sub>S</sub> =300 KΩ V <sub>COIN</sub> =5 <sup>±2.5</sup> V	10		0.7		%		
	Linearity	R <sub>S</sub> =500 KΩ V <sub>COIN</sub> =7.5 <sup>±5</sup> V	15		0.9				
Vz	Zener Diode Voltage	I <sub>Z</sub> = 50 μA		4.45	5.5	7.5	V		
Rz	Zener Dynamic Resistance	$I_Z = 1 \text{ mA}$			40		Ω		
PHASE	COMPARATOR SECTION				1				
R14	Pin 14 (signal in) Input		5	1	2				
	Resistance		10	0.2	0.4		M		
			15	0.1	0.2				
	A.C. Coupled Signal Input	f <sub>in</sub> = 100 KHz sine wave	5	180	360				
	Voltage Sensitivity *		10	330	660		m٧		
	(peak to paek)		15	900	1800				

ELECTRICAL	CHARACTERISTICS	(continued)
------------	-----------------	-------------

Sympol	Devementer	Test Conditions		Value		Unit	
Symbol	Parameter —	V <sub>DD</sub> (\	) Min.	Тур.	Max.	Unit	
PHASE	COMPARATOR SECTION (cont'd)	·					
T <sub>PHL</sub>	Propagation Delay Time High to	5	225	450			
	Low Level Pins 14 to 13	10	100	200		ns	
		15	65	130			
T <sub>PLH</sub>	Propagation Delay Time Low to	5		350	700		
	High, Level	10		150	300	ns	
		15		100	200		
T <sub>PHZ</sub>	Propagation Delay Time 3-state	5		225	450		
	High Level to High Impedance Pins 14 to 13	10		100	200	ns	
	Pins 14 to 13	15		65	130		
$T_{PLZ}$	Low Level to High Impedance	5		285	570		
		10		130	260	ns	
		15		95	190		
t <sub>r</sub> , t <sub>f</sub>	Input Rise or Fall Time	5			50		
	Comparator Pin 3	10			1	μs	
		15			0.3		
	Signal Pin 14	5			500		
		10			20	μs	
		15			2.5		
$T_{THL}$ ,	Transition Time	5		100	200		
$T_{TLH}$		10		50	100	ns	
		15		40	80		

\* For sine wave the frequency must be greater than  $10 \text{KH}_{\text{Z}}$  for Phase Comparator II.

#### **DESIGN INFORMATION**

 $\begin{array}{ll} \mbox{This information is a guide for approximating the values of external components for the $HCC/HCF$ 4046B$ in a Phase-Locked-Loop system. The selected external components must be within the following ranges : $5k\Omega \le R1, R2, R_S \le 1M\Omega$ \\ \mbox{C1} \ge 100pF$ at $V_{DD} \ge 5V$ \\ \mbox{C1} \ge 50pF$ at $V_{DD} \ge 10V$ \\ \end{array}$ 

	USING PHASE (	COMPARATOR I			
CHARACTERISTICS	VCO WITHOUT	VCO WITH	VCO WITHOUT	VCO WITH	
	OFFSET R2 = ∞	OFFSET	OFFSET R2 = ∞	OFFSET	
VCO Frequency	1 max 1 0 1 min VDD2 VCD INPUT VOLTAGE 5-1479	Ymax to tmin VDD2 VDD VCO INPUT VOLTAGE 5-1480	1 max 1 0 1 min VDD2 VCD INPUT VOLTAGE 5-1579	fmax to fmin VD2 VDD VCO INPUT VOLTAGE 5-1460	
For No Signal Input	VCO in PLL System w frequency fo	ill Adjust to centre	VCO in PLL System w Operating Frequency		
Frequency Lock Range, 2 f <sub>L</sub>			frequency range <sub>nax</sub> - f <sub>min</sub>		
Frequency Capture Range, 2 f <sub>C</sub>	R3 IN O T1 = R3 C2	Ο OUT (1),(2) 2f <sub>C</sub> # <u>1</u> γ ⁄ <u>2π fL</u> ζ1	fa	= fL	
Loop Filter Component Selection	INO R3	——————————————————————————————————————	ις. 	- 'L	
Phase Angle Between Signal and Comparator	90° at Centre Frequen 0° and 180° at ends o		Always 0° in lock		
Locks on Harmonics of Centre Frequency	Ye	es	N	0	
Signal Input Noise Rejection	Hi	gh	Lo	W	

\* G.S. Mosckytz "miniaturized RC filters using phase Lockedloop" BSTJ, may 1965

DIM.		mm		inch				
Dini	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.		
a1	0.51			0.020				
В	0.77		1.65	0.030		0.065		
b		0.5			0.020			
b1		0.25			0.010			
D			20			0.787		
E		8.5			0.335			
е		2.54			0.100			
e3		17.78			0.700			
F			7.1			0.280		
I			5.1			0.201		
L		3.3			0.130			
Z			1.27			0.050		

## Plastic DIP16 (0.25) MECHANICAL DATA



DIM.		mm			inch	
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А			20			0.787
В			7			0.276
D		3.3			0.130	
E	0.38			0.015		
e3		17.78			0.700	
F	2.29		2.79	0.090		0.110
G	0.4		0.55	0.016		0.022
н	1.17		1.52	0.046		0.060
L	0.22		0.31	0.009		0.012
М	0.51		1.27	0.020		0.050
N			10.3			0.406
Р	7.8		8.05	0.307		0.317
Q			5.08			0.200

### Ceramic DIP16/1 MECHANICAL DATA



DIM.		mm			inch	
Dim.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А	9.78		10.03	0.385		0.395
В	8.89		9.04	0.350		0.356
D	4.2		4.57	0.165		0.180
d1		2.54			0.100	
d2		0.56			0.022	
E	7.37		8.38	0.290		0.330
е		1.27			0.050	
e3		5.08			0.200	
F		0.38			0.015	
G			0.101			0.004
м		1.27			0.050	
M1		1.14			0.045	

## PLCC20 MECHANICAL DATA



Information furnished is believed to be accurate and reliable. However, SGS-THOMSON Microelectronics assumes no responsability for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may results from its use. No license is granted by implication or otherwise under any patent or patent rights of SGS-THOMSON Microelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. SGS-THOMSON Microelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of SGS-THOMSON Microelectonics.

© 1994 SGS-THOMSON Microelectronics - All Rights Reserved

SGS-THOMSON Microelectronics GROUP OF COMPANIES Australia - Brazil - France - Germany - Hong Kong - Italy - Japan - Korea - Malaysia - Malta - Morocco - The Netherlands -Singapore - Spain - Sweden - Switzerland - Taiwan - Thailand - United Kingdom - U.S.A